

Features:

- Broad band operation from 10MHz to 6 GHz
- PIN diode limiter protected input prevent input over drive damage
- SMA female connector I/O
- Single DC power supply, internal voltage regulator, operating voltage from +9.5~+15V
- Operating temperature -40~+85°C, storage temperature -55~+125°C

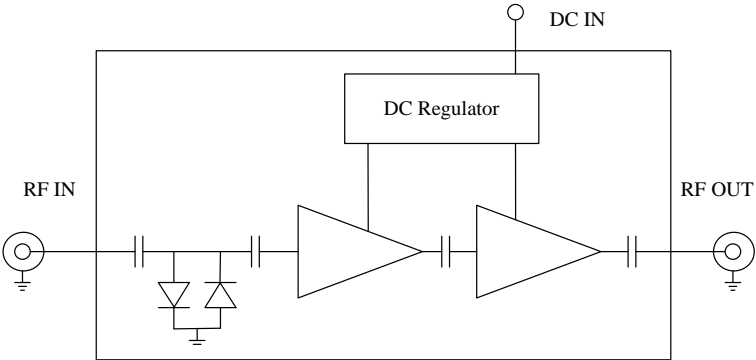
**General Description**

ABL0600-01-3040DP is a two stage InGaP/GaAs HBT based broadband low noise amplifier module with input PIN diode limiter protection. It operates in the frequency from 10MHz to 6.0 GHz and provides 34dB of typical small signal gain with 3.0dB typical noise figure, excellent gain flatness, as well as good VSWR at both input and output. The amplifier requires only a single DC power supply. Its built-in voltage regulator allows the amplifier being used at DC voltage as low as 9.5V to as high as +15V.

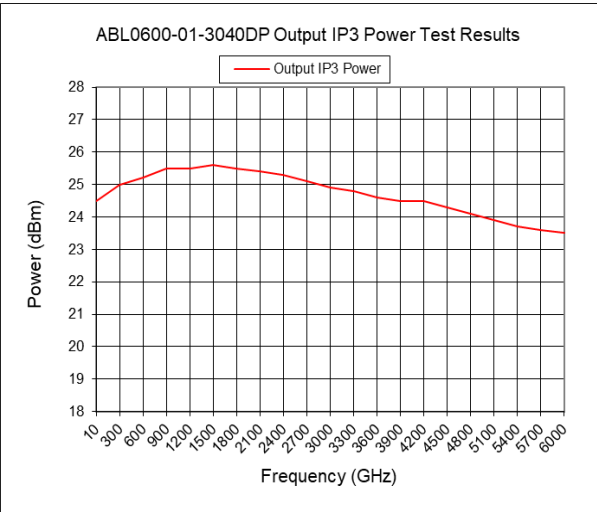
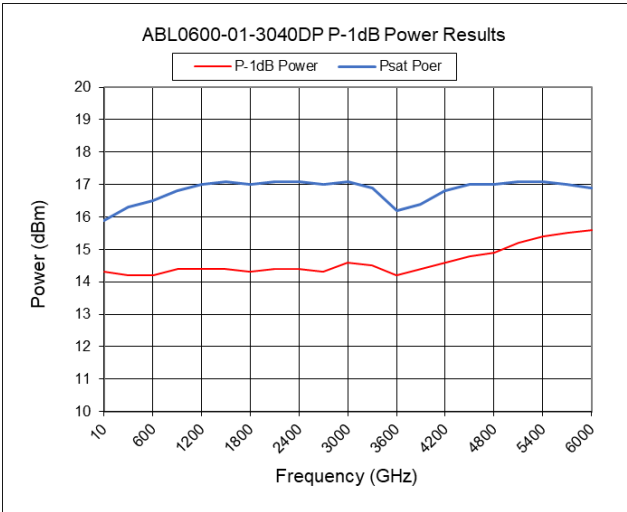
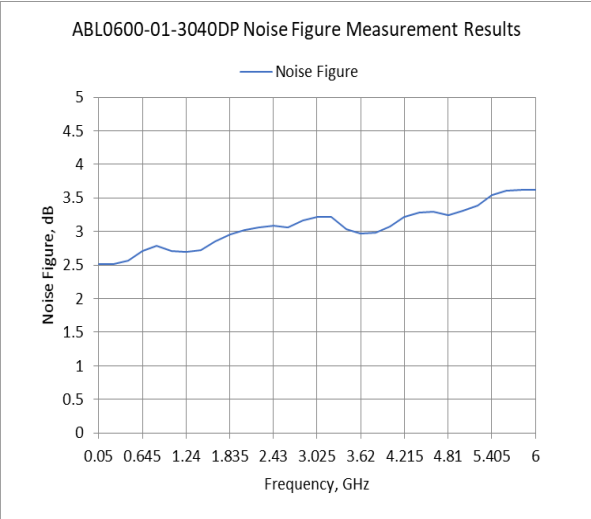
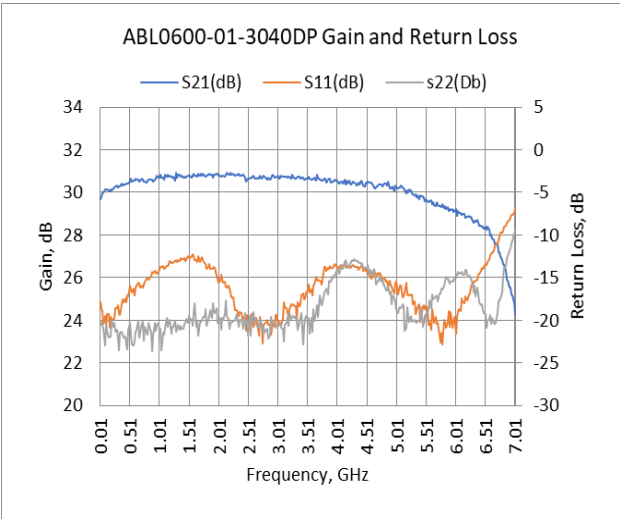
Electrical Specifications

Parameters	Units	Specifications		
		Minimum	Typical	Maximum
Frequency Range	MHz	10.0		6000.0
Noise Figure (from 50MHz) @25°C	dB		3.5	4.5
Nominal SS Gain @25°C	dB	27.0	30.0	33.0
Gain flatness	dB		+/-1.0	+/-1.25
Gain Variation	dB		+/-1.0	
P-1dB Compression Point	dBm	+12.5	+14.5	
Saturated Output power	dBm	+15.5	+16.5	
Output 3 rd order intercept point power, tested with two tones spaced 1MHz apart	dBm	+33.0	+37.0	
Input VSWR	-		1.5:1	2.0:1
Output VSWR	-		1.5:1	2.0:1
Reverse Isolation	dB	40.0	45.0	
Spurious	dBc			-60.0
Input no damage power	dBm	+30.0		
Operating Temperature	°C	-40.0		+85.0
Survival Temperature	°C	-55.0		+125.0
DC Voltage	V	+9.5	+12.0	+15.0
DC Supply Current	mA	90.0	100.0	120.0
In/Out connectors	-	50 ohm SMA female		
Size	inches	1.70×0.95×0.375		

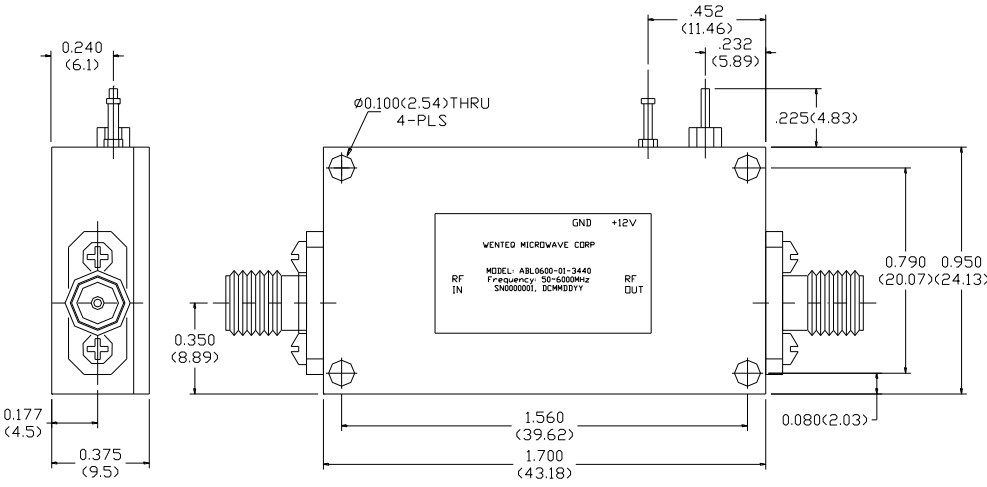
Functional Diagram



Typical Test Results



Mechanical Structure:



Note: All units in inches (mm).

Housing Material and Surface Finish:

- Body and cover material: aluminum
- Surface finish: nickel plated
- Connector material: Copper
- Connector surface finish: gold plated

Absolute Maximum Ratings

DC Voltage	+15V
RF Input Power	+30 dBm
DC Voltage at RF I/O	±25V
Storage Temperature	-55~+125°C
Operating Temperature	-40~+85°C

Revision History:

Revision	Date	Description	Comments
A00	01/08/2020	Initial Release	
A01	05/18/2023	Input Limiter Change	



Electrostatic sensitive device, please observe precautions for handling this amplifier.